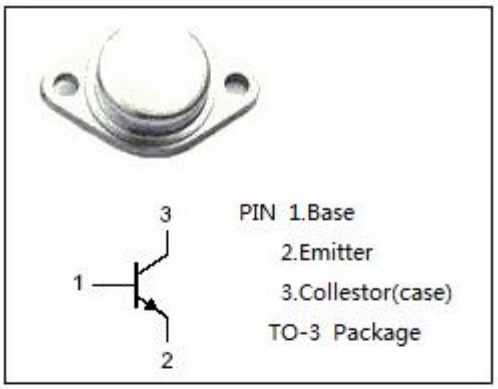
isc Silicon NPN Power Transistor 2SD73

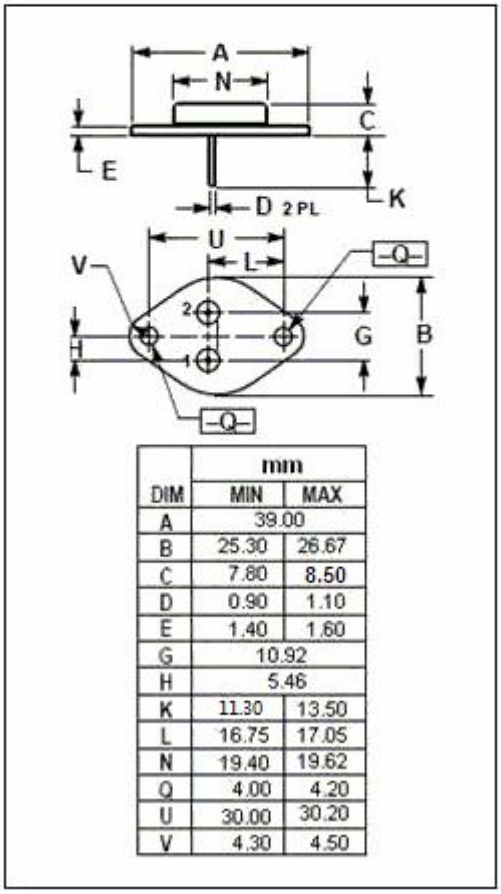
DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 100V(Min)
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for use in general purpose power amplifier and switching applications



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	8	A
P_C	Collector Power Dissipation @ T_C=25℃	60	W
T_J	Junction Temperature	175	℃
T_{stg}	Storage Temperature Range	-65~175	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 30mA; I_B= 0	100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 0.5A			2.0	V
$V_{BE(on)}$	Base -Emitter On Voltage	I_C= 1A; V_{CE}= 5V			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 100V; I_E= 0			100	uA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			100	uA
h_{FE-1}	DC Current Gain	I_C= 1A; V_{CE}= 5V	60		200	
h_{FE-2}	DC Current Gain	I_C= 4A; V_{CE}= 5V	20			
f_T	Current-Gain—Bandwidth Product	I_C= 1A; V_{CE}= 5V		20		MHz